

N-channel 25 V, 6.75 mΩ logic level MOSFET in LFPAK56 using NextPowerS3 Technology

6 April 2016

**Product data sheet** 

### 1. General description

Logic level gate drive N-channel enhancement mode MOSFET in LFPAK56 package. NextPowerS3 portfolio utilising Nexperia's unique "SchottkyPlus" technology delivers high efficiency, low spiking performance usually associated with MOSFETS with an integrated Schottky or Schottky-like diode but without problematic high leakage current. NextPowerS3 is particularly suited to high efficiency applications at high switching frequencies.

### 2. Features and benefits

- Ultra low Q<sub>G</sub>, Q<sub>GD</sub> and Q<sub>OSS</sub> for high system efficiency, especially at higher switching frequencies
- Superfast switching with soft-recovery; s-factor > 1
- Low spiking and ringing for low EMI designs
- Unique "SchottkyPlus" technology; Schottky-like performance with < 1 µA leakage at 25 °C
- Optimised for 4.5 V gate drive
- Low parasitic inductance and resistance
- High reliability clip bonded and solder die attach Power SO8 package; no glue, no wire bonds, qualified to 175 °C
- Wave solderable; exposed leads for optimal visual solder inspection

### 3. Applications

- On-board DC:DC solutions for server and telecommunications
- Secondary-side synchronous rectification in telecommunication applications
- Voltage regulator modules (VRM)
- Point-of-Load (POL) modules
- Power delivery for V-core, ASIC, DDR, GPU, VGA and system components
- Brushed and brushless motor control

### 4. Quick reference data

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	-	25	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	-	61	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	-	-	43	W



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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Tj	junction temperature		-55	-	175	°C
Static chara	acteristics		ł	1		
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 25 °C; Fig. 10	-	8.29	10.19	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	5.84	6.75	mΩ
Dynamic ch	aracteristics			1		
Q <sub>G(tot)</sub> tota	total gate charge	I <sub>D</sub> = 15 A; V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 10 V; Fig. 12; Fig. 13	-	10.5	-	nC
		I <sub>D</sub> = 15 A; V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 4.5 V; Fig. 12; Fig. 13	-	4.9	-	nC
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	5.6	-	nC
Q <sub>GD</sub>	gate-drain charge	I <sub>D</sub> = 15 A; V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 4.5 V; Fig. 12; Fig. 13	-	1.1	-	nC
Source-drai	in diode	· · ·	1			
S	softness factor	$I_{S} = 15 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$ $\text{V}_{DS} = 12 \text{ V}; \text{ Fig. 16}$	-	1.1	-	

# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source		G LET A
4	G	gate	ប្រុប្បូប	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

## 6. Ordering information

Table 3.       Ordering information							
Type number Package							
	Name	Description	Version				
PSMN6R0-25YLD	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669				

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### 7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN6R0-25YLD	6D025L

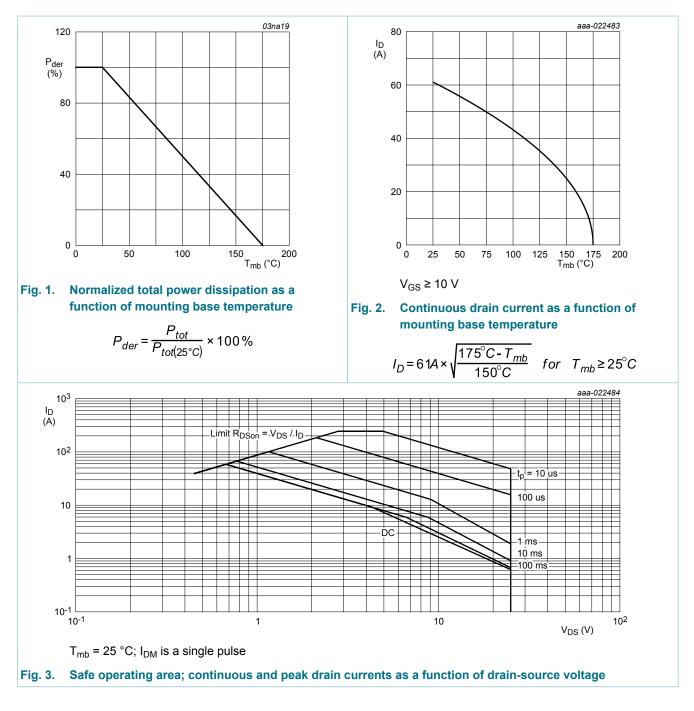
### 8. Limiting values

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	25	V
V <sub>DGR</sub>	drain-gate voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ		-	25	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	43	W
ID	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	61	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>		-	43	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; Fig. 3		-	244	Α
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ		300	-	V
Source-dra	in diode	1				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	36	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$		-	244	Α
Avalanche	ruggedness	1	1			
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 15 A; V <sub>sup</sub> ≤ 25 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; unclamped; t <sub>p</sub> = 209 μs	[1]	-	50.9	mJ

[1] Protected by 100% test

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### 9. Thermal characteristics

Table 6. TI	hermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 4	-	3.1	3.5	K/W

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance	Fig. 5	-	50	-	K/W
	from junction to ambient	<u>Fig. 6</u>	-	125	-	K/W

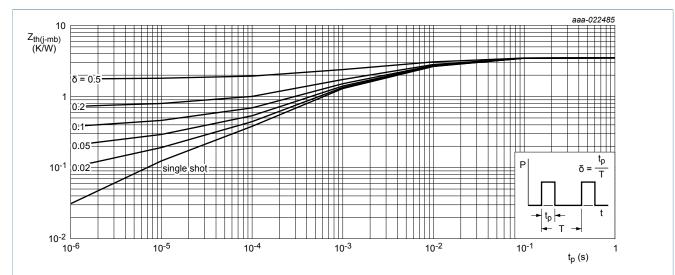
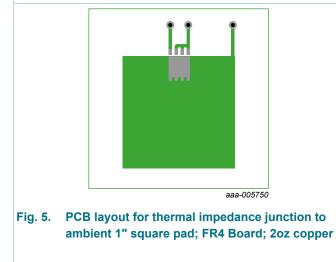


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration



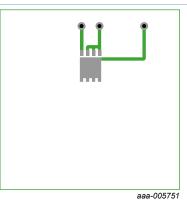


Fig. 6. PCB layout for thermal resistance junction to ambient minimum footprint; FR4 Board; 2oz copper

### **10. Characteristics**

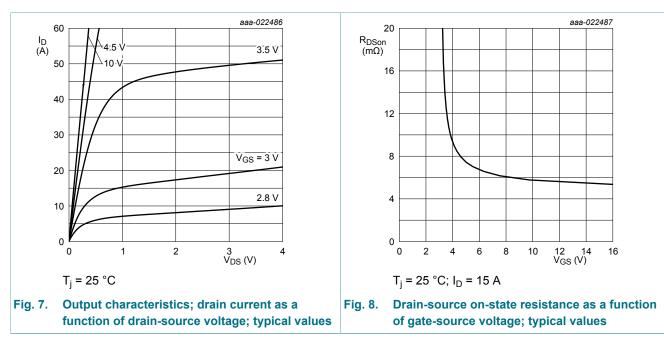
Table 7. C	haracteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	Static characteristics					
V <sub>(BR)DSS</sub> drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	25	-	-	V	
	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	22.5	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_{D}$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_{j}$ = 25 °C	1.2	1.76	2.2	V

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
ΔV <sub>GS(th)</sub> /ΔT	gate-source threshold voltage variation with temperature	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	-4.2	-	mV/K
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 20 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-	1	μA
		$V_{DS}$ = 20 V; $V_{GS}$ = 0 V; $T_j$ = 125 °C	-	0.89	-	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	8.29	10.19	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 175 °C; Fig. 10; Fig. 11	-	-	17.32	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; Fig. 10	-	5.84	6.75	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 175 °C; Fig. 10; Fig. 11	-	-	11.48	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	-	0.68	-	Ω
Dynamic cha	aracteristics					
Q <sub>G(tot)</sub>	Q <sub>G(tot)</sub> total gate charge	I <sub>D</sub> = 15 A; V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 10 V; Fig. 12; Fig. 13	-	10.5	-	nC
		I <sub>D</sub> = 15 A; V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 4.5 V; Fig. 12; Fig. 13	-	4.9	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	5.6	-	nC
Q <sub>GS</sub>	gate-source charge	$I_D$ = 15 A; $V_{DS}$ = 12 V; $V_{GS}$ = 4.5 V;	-	2.3	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	Fig. 12; Fig. 13	-	1.2	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge		-	1.1	-	nC
Q <sub>GD</sub>	gate-drain charge		-	1.1	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 15 A; V <sub>DS</sub> = 12 V; <u>Fig. 12</u> ; <u>Fig. 13</u>	-	3	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	705	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 14</u>	-	598	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	46	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 12 V; R <sub>L</sub> = 1 Ω; V <sub>GS</sub> = 4.5 V;	-	7.6	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$	-	7.4	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	7.6	-	ns
t <sub>f</sub>	fall time	1	-	4.5	-	ns

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Q <sub>oss</sub>	output charge	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 12 V; f = 1 MHz; T <sub>j</sub> = 25 °C		-	9.3	-	nC
Source-dra	in diode	1					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 15 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <u>Fig. 15</u>		-	0.82	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S}$ = 15 A; dI_{S}/dt = -100 A/µs; V_{GS} = 0 V;		-	20.2	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 12 V; <u>Fig. 16</u>	[1]	-	10	-	nC
t <sub>a</sub>	reverse recovery rise time			-	9.4	-	ns
t <sub>b</sub>	reverse recovery fall time			-	10.8	-	ns
S	softness factor			-	1.1	-	

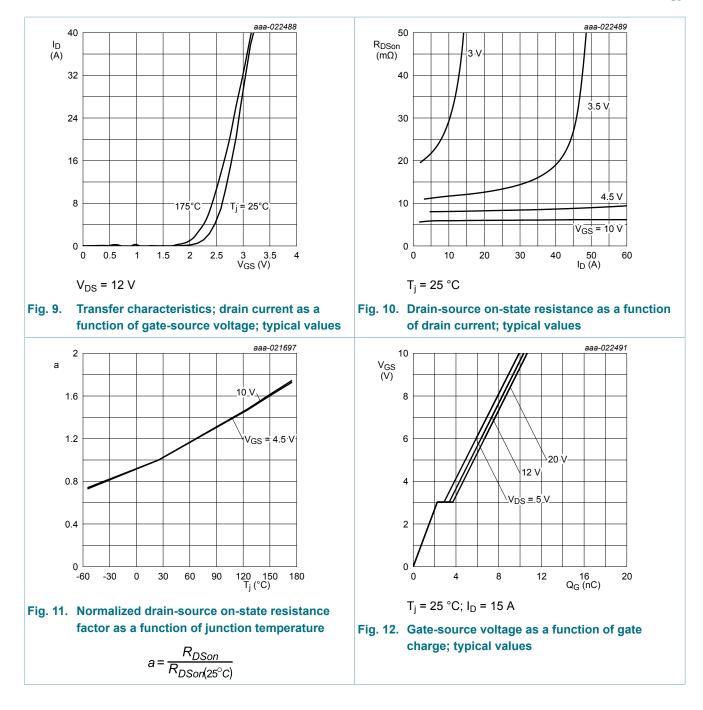


[1] includes capacitive recovery

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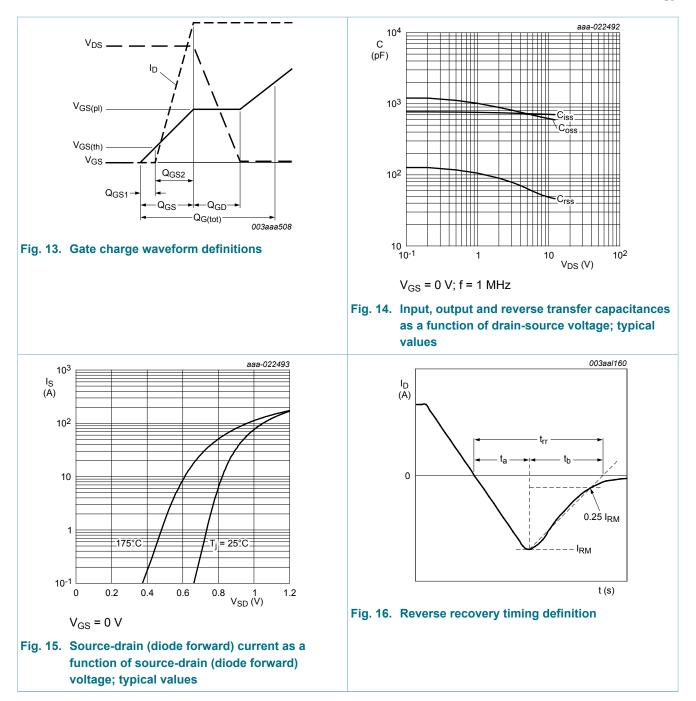
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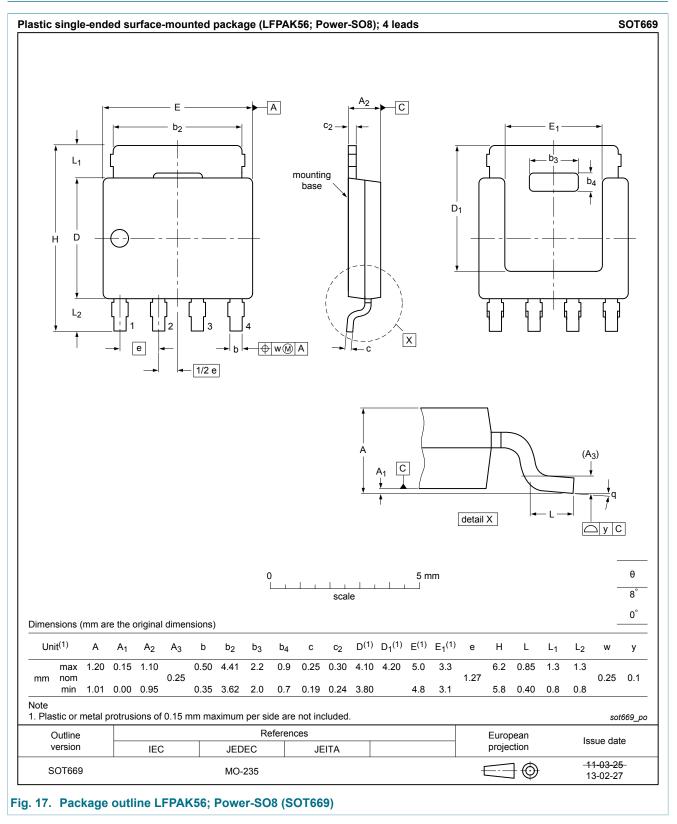
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#### N-channel 25 V, 6.75 mΩ logic level MOSFET in LFPAK56 using NextPowerS3 Technology

### **11. Package outline**



PSMN6R0-25YLD

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### 12. Legal information

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